

## Process Change Notice

**Parts Affected:**

Chip process CPD41, High Current Switching Diode discrete semiconductors, wafers, and die in chip form.

**Extent of Change:**

An overall reduction of the die area.

The CPD41 chip process currently measures 20 x 20 mils and is being replaced by the CPD93V chip process which measures 12.8 x 12.8 mils.

**Reason for Change:**

To accommodate assemblies of extremely small surface mount, epoxy molded packages.

**Effect of Change:**

This change does not affect the electrical characteristics of any device.

**Effective Date of Change:**

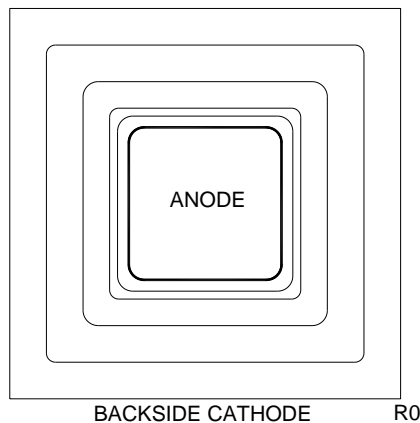
Existing inventory will be shipped until depleted.

**Sample Availability:**

Please contact Salesperson or Manufacturer's Representative.

**Figures:**

**CPD93V Chip Geometry**



Die Size:	12.8 x 12.8 mils
Die Thickness:	7.1 mils
Bond Pad Area (Anode):	5.1 x 5.1 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au.As/Au (10,000Å)



145 Adams Avenue, Hauppauge, NY 11788 USA  
Tel: (631) 435-1110 • Fax: (631) 435-1824  
[www.centrialsemi.com](http://www.centrialsemi.com)  
<mailto:processchange@centrialsemi.com>  
<http://www.centrialsemi.com/processchange>

**PCN # 109**

**Notification Date:**

**21 April 2009**

**Part Numbers Affected:**

CPD41-BAS56-WN  
CPD41-CEN923-CT  
CPD41-CMPD4150-WR  
CPD41-CMPD4150-WS  
CPD41-CMPD914-WN  
CPD41-1N3600-WN  
CPD41-1N4148-CT  
CPD41-1N4150-CT  
CPD41-1N4150-WN

CMPD4150  
CMHD4150  
BAS56